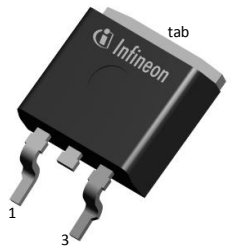
MOSFET

OptiMOS™ Power Transistor, -60 V

D²PAK



Features

- P-Channel
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- 100% avalanche tested
- Logic Level
- Enhancement mode
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product Validation:
Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

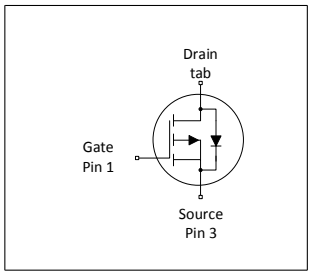


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on),max}$	11	mΩ
I_D	-100	A

Type / Ordering Code	Package	Marking	Related Links
IPB06P001L	PG-TO 263-3	06P001L	-

Table of Contents

1 Maximum ratings

at T_C=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- - - -	- - - -	-100 -78 -91 -65	A	V_{GS}=-10 V, T_C=25 °C V_{GS}=-10 V, T_C=100 °C V_{GS}=-4.5 V, T_C=25°C V_{GS}=-4.5 V, T_C=100 °C
Pulsed drain current[1)]	$I_{D,pulse}$	-	-	-400	A	T_C=25 °C
Avalanche energy, single pulse[2)]	E_{AS}	-	-	1616	mJ	I_D=-100 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	300	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	0.5	°C/W	-
Device on PCB, 6 cm² cooling area[3)]	R_{thJA}	-	-	62	°C/W	-

[1)] See Diagram 3 for more detailed information
[2)] See Diagram 13 for more detailed information
[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60	-	-	V	V_{GS}=0 V, I_D=-250 µA
Gate threshold voltage	$V_{GS(th)}$	-1	-1.5	-2	V	V_{DS}=V_{GS}, I_D=-5550 µA
Zero gate voltage drain current	I_{DSS}	- -	-0.1 -10	1 -100	µA	V_{DS}=-60 V, V_{GS}=0 V, T_j=25 °C V_{DS}=-60 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	V_{GS}=-20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	9 11	11 16	mΩ	V_{GS}=-10 V, I_D=-100 A V_{GS}=-4.5 V, I_D=-91 A
Gate resistance	R_G	-	5	-	Ω	-
Transconductance	g_{fs}	-	100	-	S	|V_{DS}|≥2|I_D|$R_{DS(on)max}$, I_D=-50 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	8500	-	pF	V_{GS}=0 V, V_{DS}=-30 V, f=1 MHz
Output capacitance	C_{oss}	-	1200	-	pF	V_{GS}=0 V, V_{DS}=-30 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	260	-	pF	V_{GS}=0 V, V_{DS}=-30 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	22	-	ns	V_{DD}=-30 V, V_{GS}=-10 V, I_D=-50 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	33	-	ns	V_{DD}=-30 V, V_{GS}=-10 V, I_D=-50 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	277	-	ns	V_{DD}=-30 V, V_{GS}=-10 V, I_D=-50 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	74	-	ns	V_{DD}=-30 V, V_{GS}=-10 V, I_D=-50 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	-30	-	nC	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Gate charge at threshold	$Q_{g(th)}$	-	-13	-	nC	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Gate to drain charge	Q_{gd}	-	-76	-	nC	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Switching charge	Q_{sw}	-	-92	-	nC	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Gate charge total	Q_g	-	-281	-	nC	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Gate plateau voltage	$V_{plateau}$	-	-3.5	-	V	V_{DD}=-30 V, I_D=-100 A, V_{GS}=0 to -10 V
Output charge	Q_{oss}	-	-88	-	nC	V_{DD}=-30 V, V_{GS}=0 V

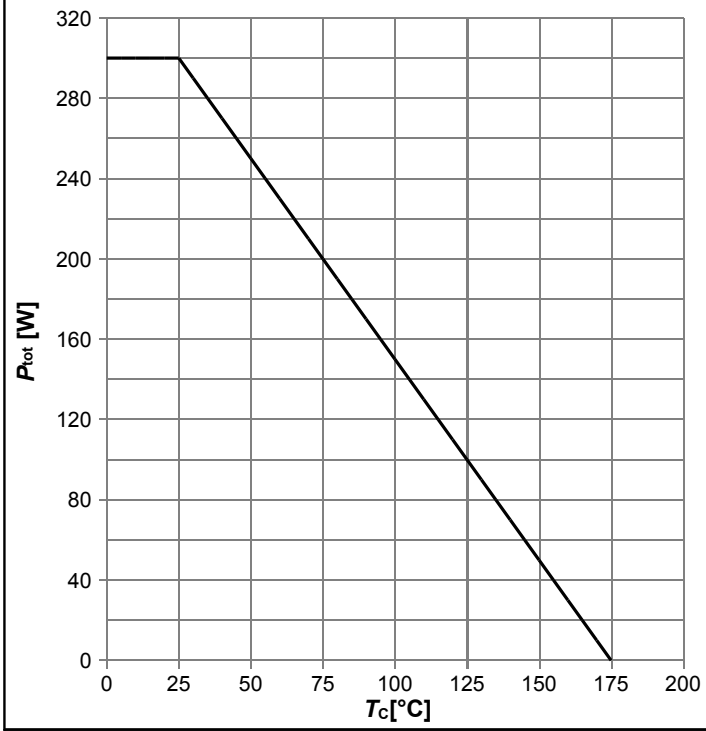
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-100	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	-400	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	-0.9	-1.2	V	V_{GS}=0 V, I_F=-100 A, T_j=25 °C
Reverse recovery time	t_{rr}	-	88	-	ns	V_R=-30 V, I_F=-100 A, di_F/dt=-100 A/µs
Reverse recovery charge	Q_{rr}	-	-324	-	nC	V_R=-30 V, I_F=-100 A, di_F/dt=-100 A/µs

[1)] See Diagram ″Gate charge waveforms″ for gate charge parameter definition

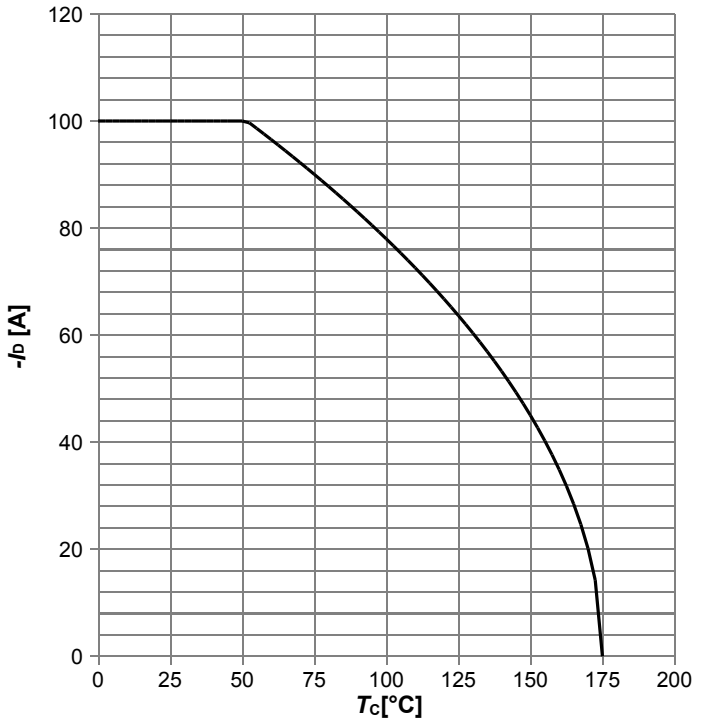
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



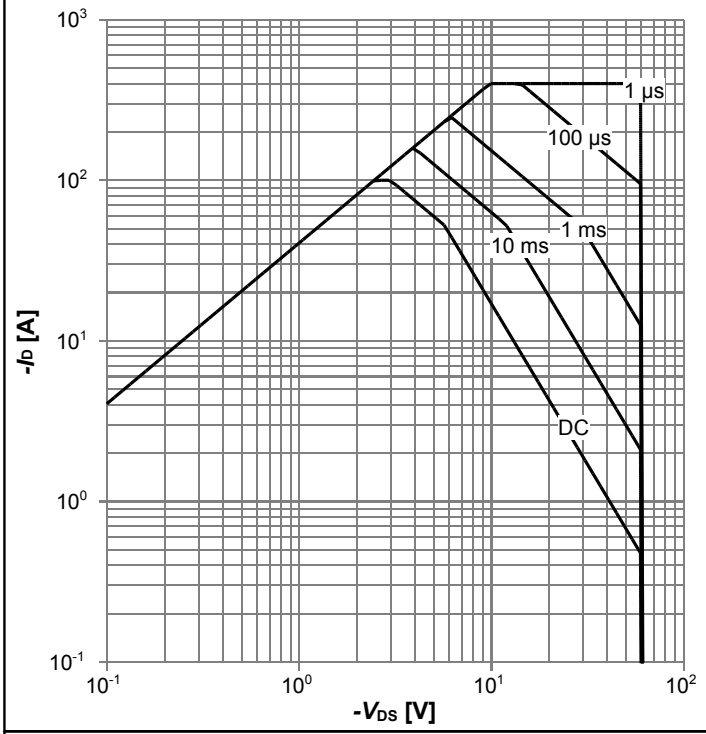
$P_{tot}=f(T_C)$

Diagram 2: Drain current



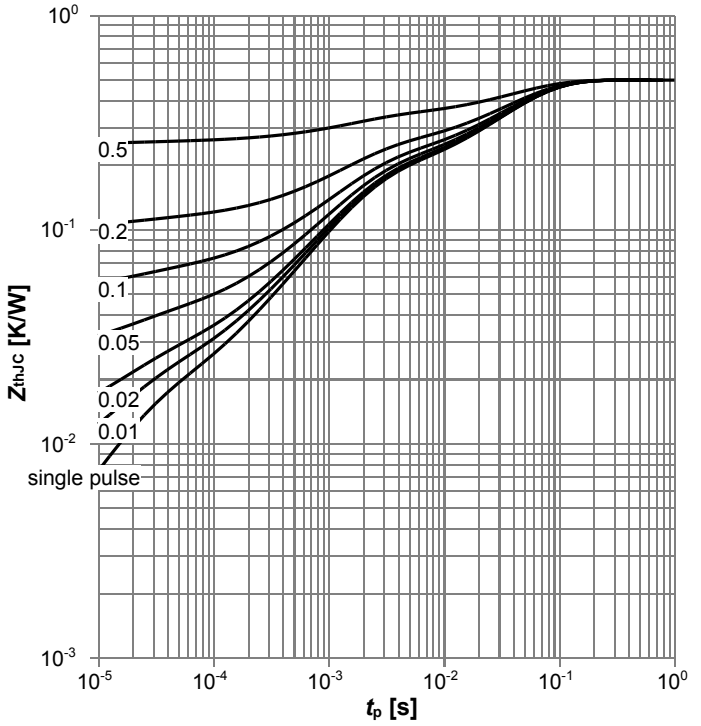
$I_D=f(T_C)$; $|V_{GS}|\geq 10$ V

Diagram 3: Safe operating area



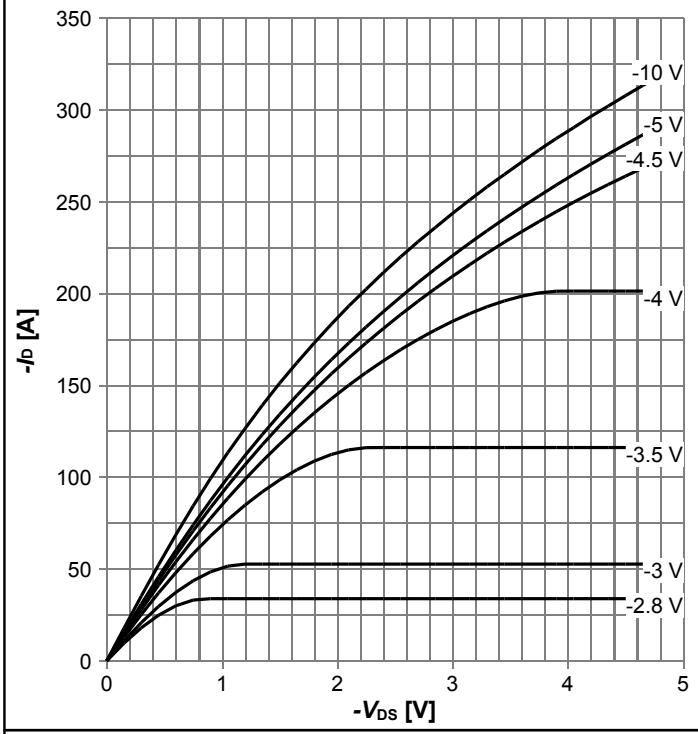
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



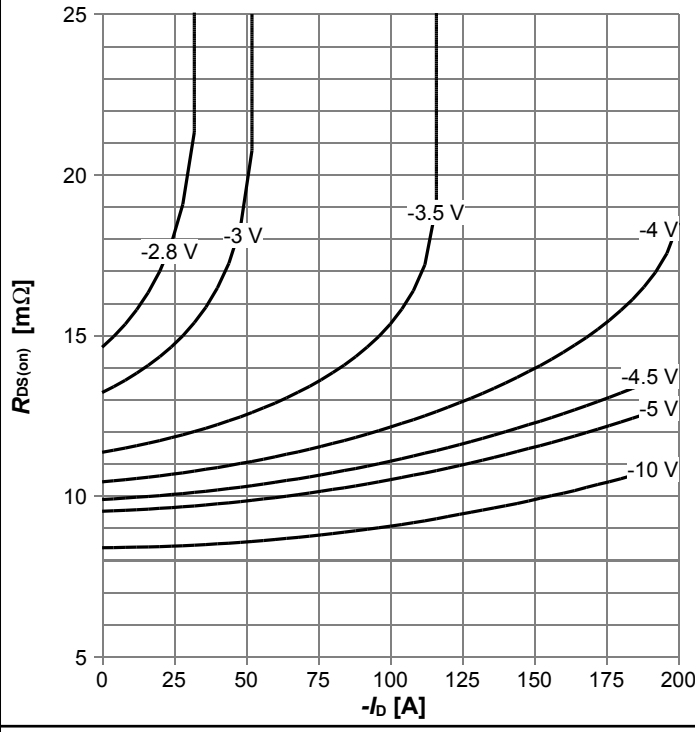
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



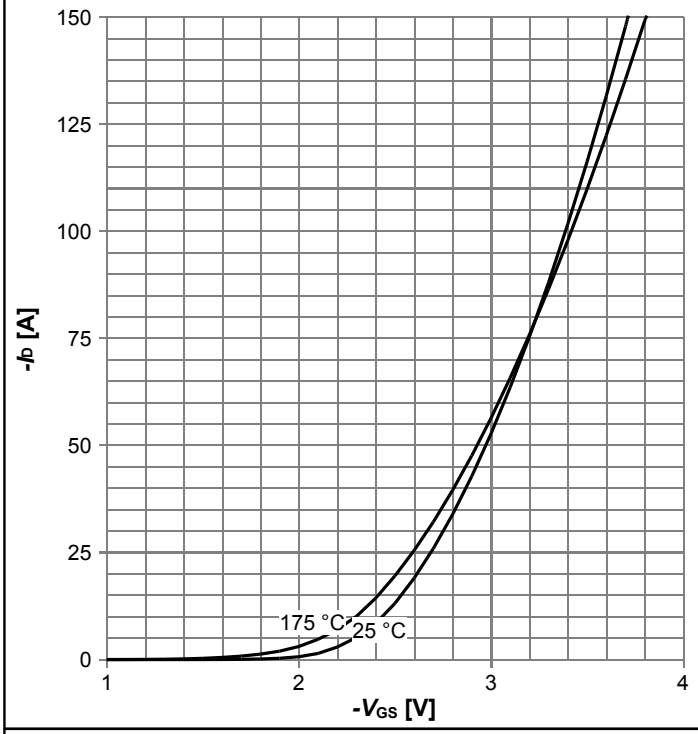
$I_D=f(V_{DS})$, $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



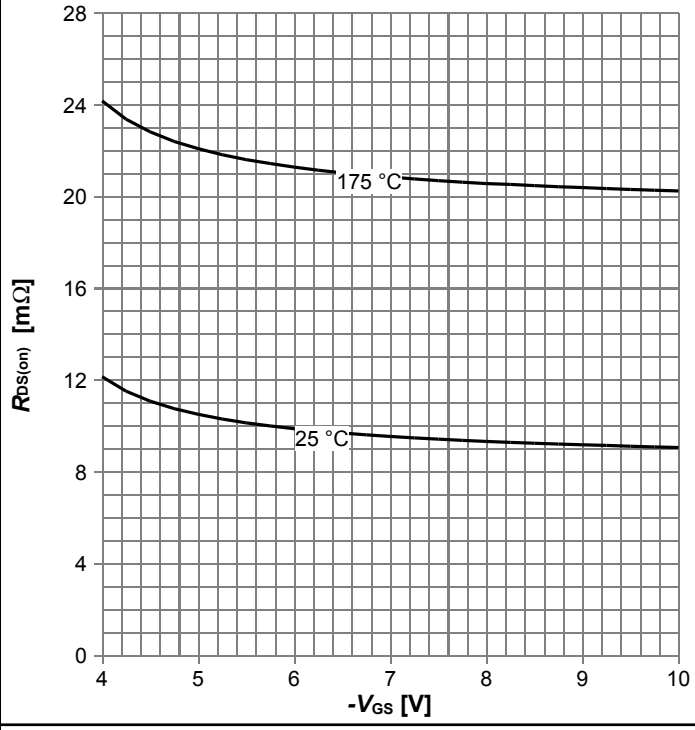
$R_{DS(on)}=f(I_D)$, $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



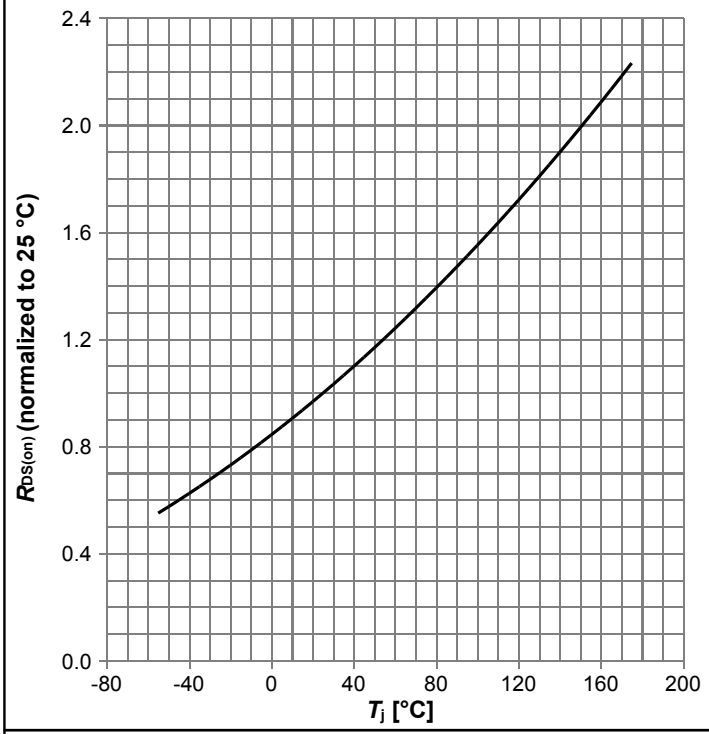
$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



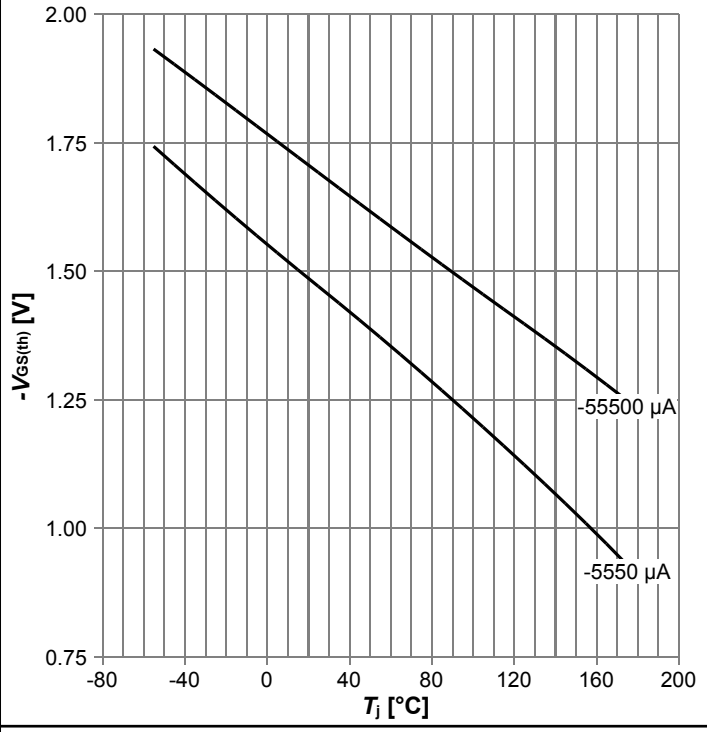
$R_{DS(on)}=f(V_{GS})$, I_D=-100 A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



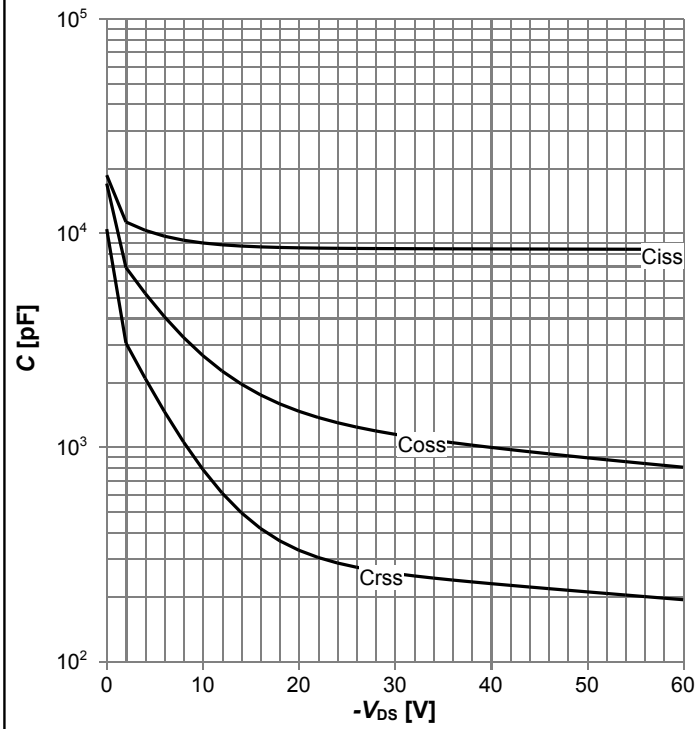
$R_{DS(on)}$=f(T_j), I_D=-100 A, V_{GS}=-10 V

Diagram 10: Typ. gate threshold voltage



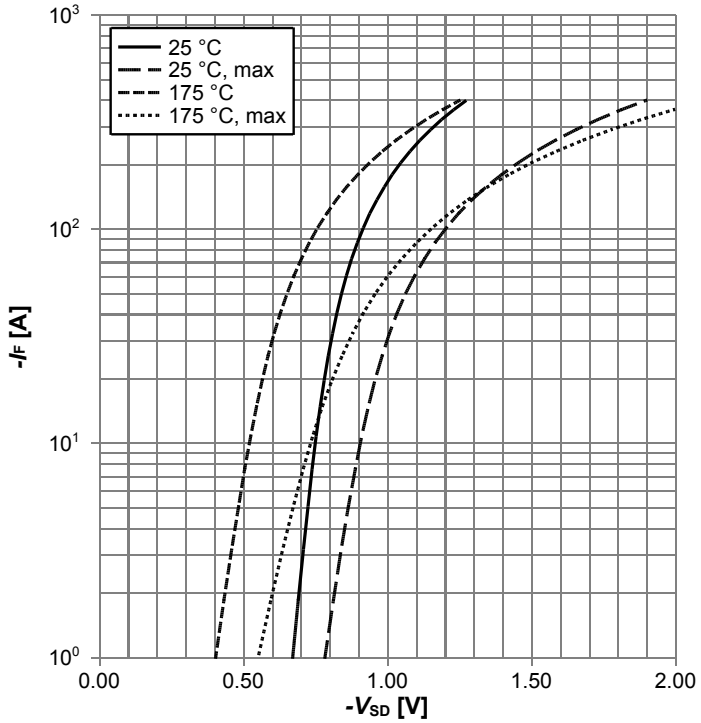
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



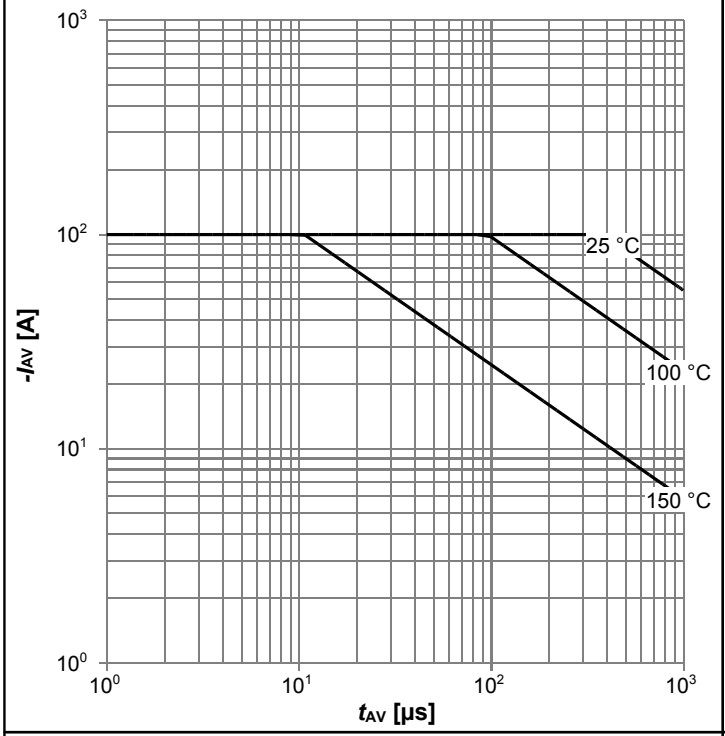
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



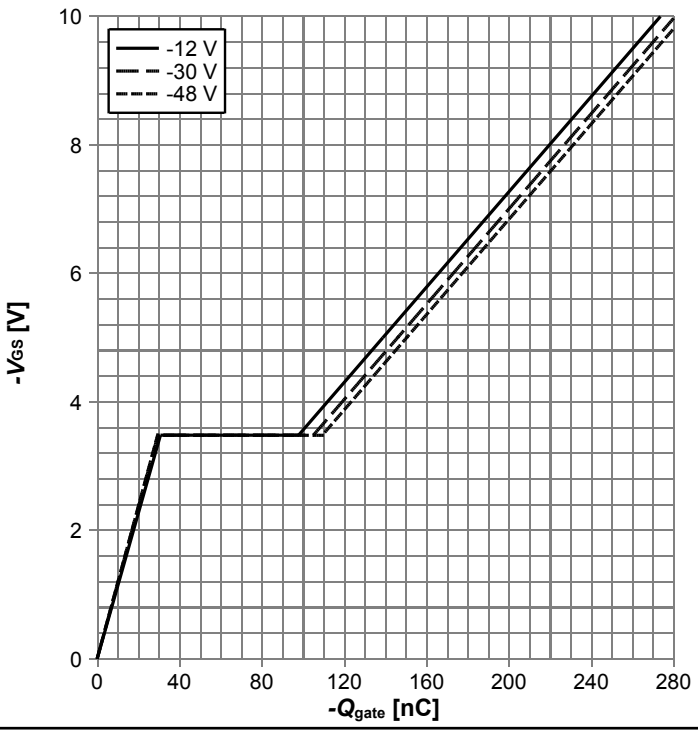
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



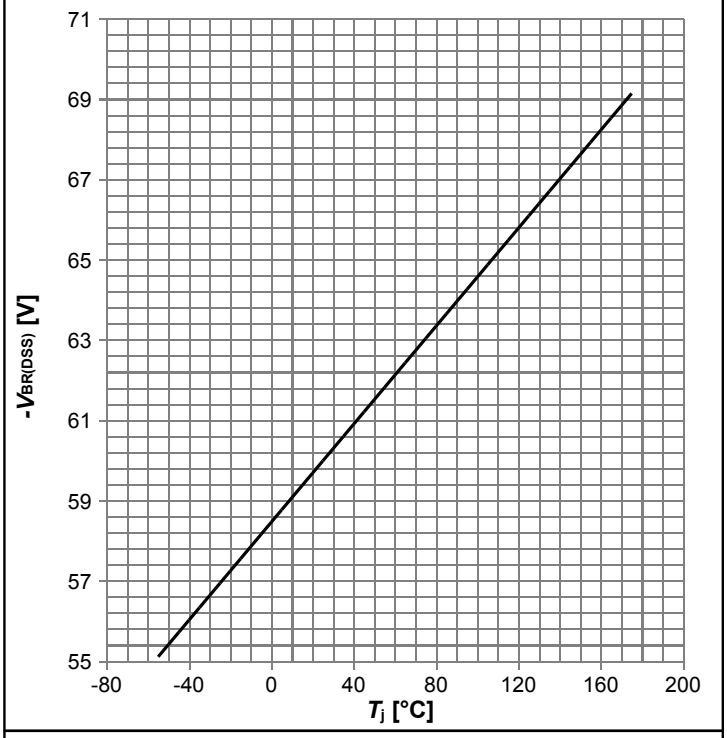
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



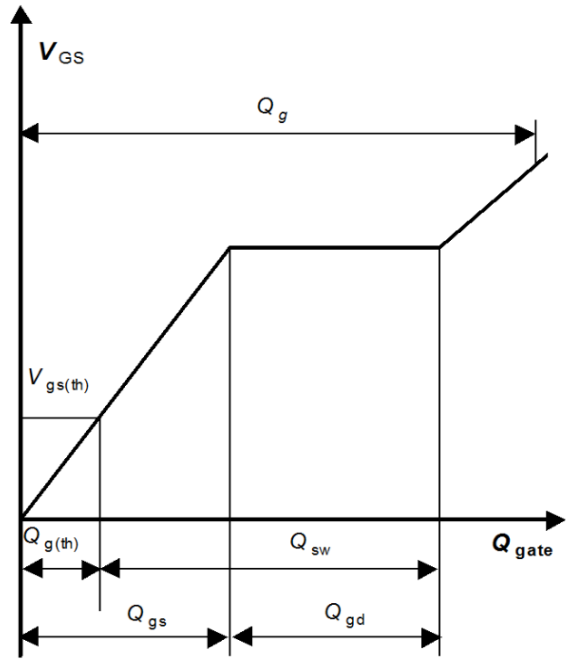
V_{GS}=f(Q_{gate}), I_D=-100 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

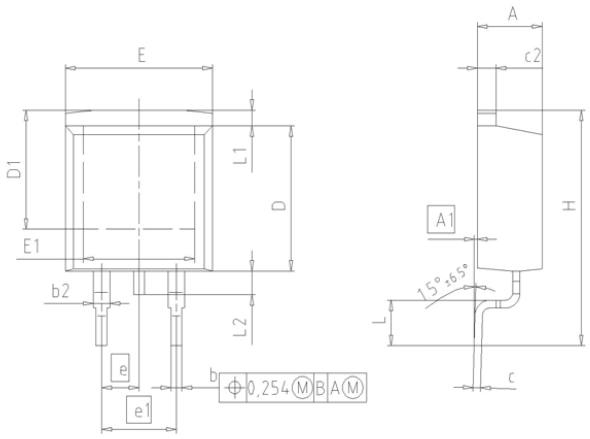


$V_{BR(DSS)}$=f(T_j); I_D=-250 µA

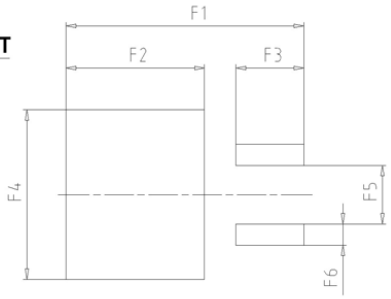
Diagram Gate charge waveforms



5 Package Outlines



FOOTPRINT



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

DOCUMENT NO.
Z8B00003324

SCALE
0 5 5
7.5mm

EUROPEAN PROJECTION

ISSUE DATE
30-08-2007

REVISION
01

Figure 1 Outline PG-TO 263-3, dimensions in mm/inches - Industrial Grade

Revision History

IPB06P001L

Revision: 2018-08-21, Rev. 2.1

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2018-05-09	Release of final version
2.1	2018-08-21	Amend typo error

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